



flowPIM 1

600 V / 50 A

Topology features

- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor
- Converter+Brake+Inverter

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

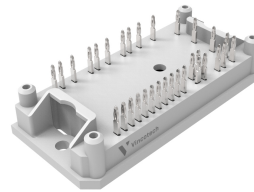
Target applications

- Industrial drives
- Embedded drives

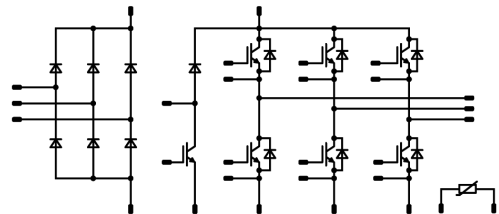
Types

- V23990-P586-A20Y

flow 1 17 mm housing



Schematic





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V23990-P586-A20Y
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
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Inverter Switch

Collector-emitter voltage	V_{CES}		600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	44	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	90	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CC} = 360\text{ V}$ $T_j = 150\text{ °C}$	6	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	39	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	100	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	68	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Brake Switch

Collector-emitter voltage	V_{CES}		600	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	64	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CC} = 360\text{ V}$ $T_j = 150\text{ °C}$	6	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$



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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Brake Diode				
Peak repetitive reverse voltage	V_{RRM}		600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	22	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	37	W
Maximum junction temperature	T_{jmax}		175	°C

Rectifier Diode

Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	44	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	270	A
Surge current capability	I^2t		370	A ² s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	56	W
Maximum junction temperature	T_{jmax}		150	°C

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	4000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min 12,7	mm
Clearance			min 12,7	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]		Min	Typ	Max	

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0008	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125	1,05	1,76 2,07	1,85 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}		0	600		25			2,6	µA
Gate-emitter leakage current	I_{GES}		20	0		25			600	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	$f = 1 \text{ Mhz}$	0	25	25			3140		pF
Output capacitance	C_{oes}							200		pF
Reverse transfer capacitance	C_{res}							93		pF

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,06		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 16 \text{ } \Omega$ $R_{goff} = 16 \text{ } \Omega$	± 15	350	50	25 125 150		187,32 185,79 186,12		ns
Rise time	t_r					25 125 150		29,43 33,19 33,33		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		230,26 252,25 257,76		ns
Fall time	t_f					25 125 150		46,24 81,64 91,61		ns
Turn-on energy (per pulse)	E_{on}					25 125 150		1,23 1,61 1,7		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,18 1,53 1,62		mWs



Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Diode

Static

Forward voltage	V_F				50	25 125	1,2	1,85 1,94	1,9 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 600$ V				25			27	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,4		K/W
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Dynamic

Peak recovery current	I_{RRM}	$di/dt=2130$ A/μs $di/dt=2041$ A/μs $di/dt=1746$ A/μs	± 15	350	50	25 125 150		32,06 41,26 44,23		A
Reverse recovery time	t_{rr}					25 125 150		161,66 221,71 240,15		ns
Recovered charge	Q_r					25 125 150		1,4 3,14 3,63		μC
Reverse recovered energy	E_{rec}					25 125 150		0,301 0,695 0,81		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		2514,84 1010,64 981,58		A/μs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Brake Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00043	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125	1,1	1,55 1,75	1,9 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,6	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	$f = 1 \text{ Mhz}$	0	25		25		1630		pF
Output capacitance	C_{oes}							108		pF
Reverse transfer capacitance	C_{res}							50		pF

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,49		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 8 \Omega$ $R_{goff} = 8 \Omega$	0/15	400	30	25 125 150		20,2 19,58 19,11		ns
Rise time	t_r					25 125 150		27,61 28,44 28,57		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		182,75 204,09 210,02		ns
Fall time	t_f					25 125 150		62,53 76,57 85,53		ns
Turn-on energy (per pulse)	E_{on}					25 125 150		0,701 0,931 0,996		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,744 0,994 1,06		mWs



Characteristic Values

Parameter	Symbol	Conditions						Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]		Min	Typ	Max	

Brake Diode

Static

Forward voltage	V_F				20	25 125		1,25	1,74 1,67	1,95 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 600$ V				25				27	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)							2,6		K/W
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Dynamic

Peak recovery current	I_{RRM}	$di/dt=860$ A/μs $di/dt=861$ A/μs $di/dt=949$ A/μs	0/15	400	30	25 125 150		10,28 13,34 14,49		A
Reverse recovery time	t_{rr}					25 125 150		167,93 242,98 263,64		ns
Recovered charge	Q_r					25 125 150		0,703 1,52 1,77		μC
Reverse recovered energy	E_{rec}					25 125 150		0,195 0,429 0,505		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		44,97 88,68 94,34		A/μs



Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Rectifier Diode

Static

Forward voltage	V_F				13	25 125		0,995 0,927	1,21 ⁽¹⁾ 1,1 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 1600$ V				25			50	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,25		K/W
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Thermistor

Static

Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 1484$ Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ± 1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ± 1 %						4000		K
Vincotech Thermistor Reference									I	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



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Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

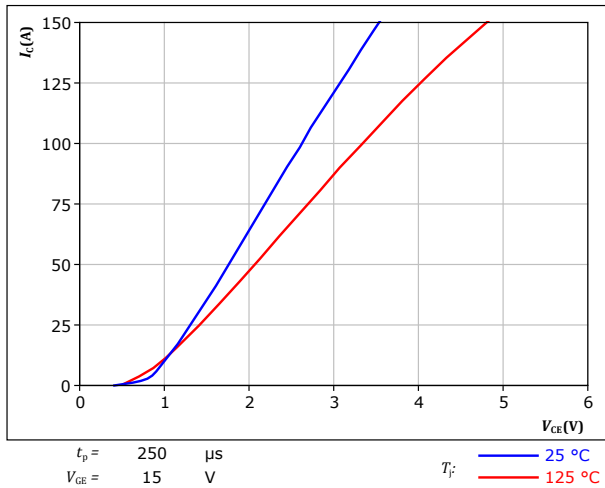


figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

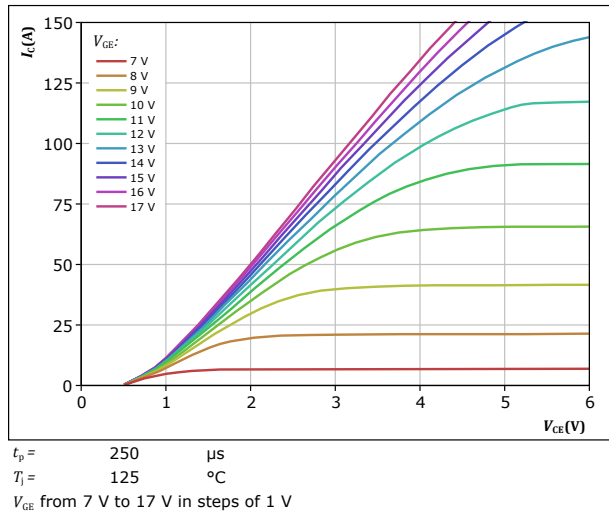


figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

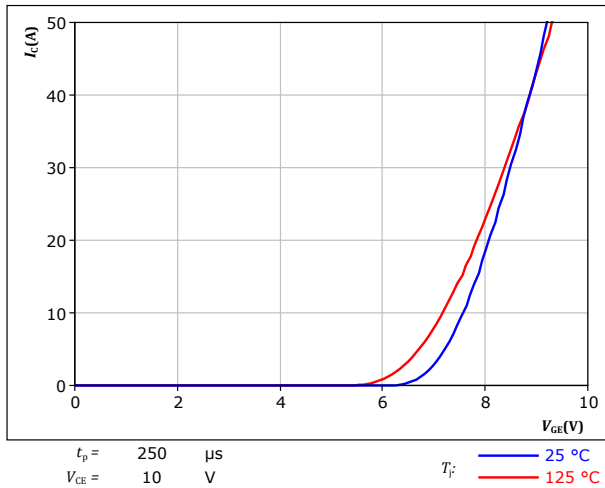
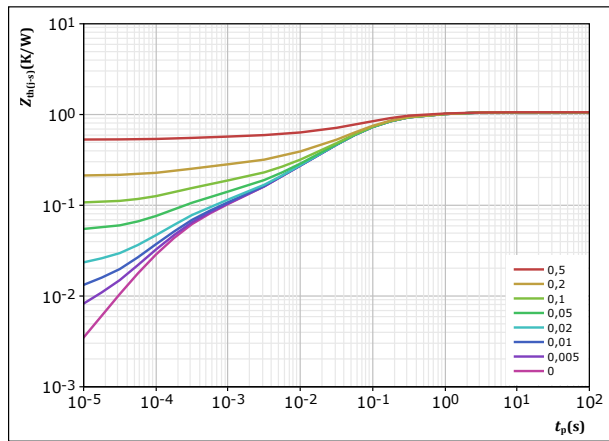


figure 4. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$





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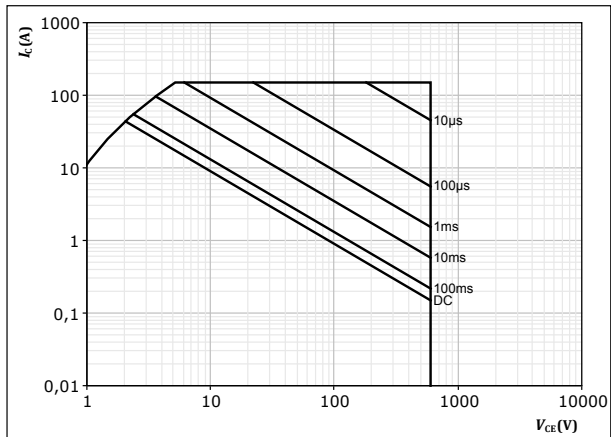
Inverter Switch Characteristics

figure 5.

IGBT

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse

$T_s = 80$ °C

$V_{GE} = 15$ V

$T_j = T_{jmax}$



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Inverter Diode Characteristics

figure 6.

FWD

Typical forward characteristics

$$I_F = f(V_F)$$

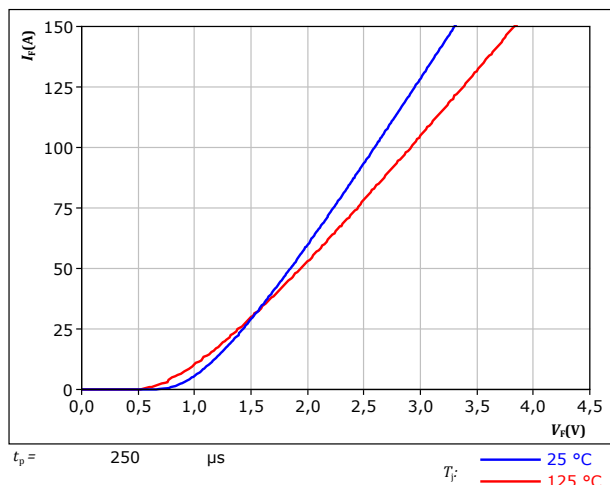
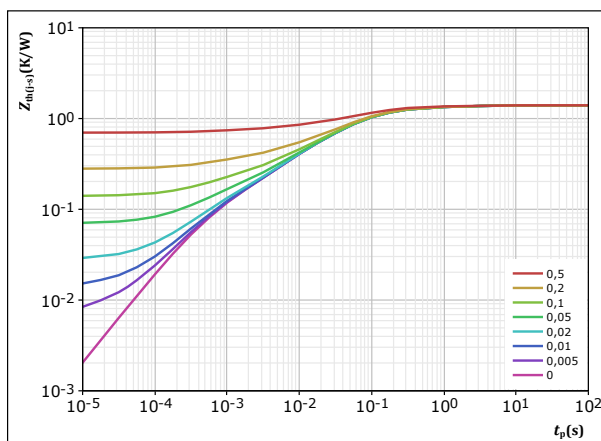


figure 7.

FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D =$	t_p / T	
$R_{th(j-s)} =$	1,399	K/W
FWD thermal model values		
R (K/W)	τ (s)	
6,76E-02	3,05E+00	
1,79E-01	3,50E-01	
6,70E-01	7,08E-02	
2,72E-01	1,81E-02	
1,35E-01	4,13E-03	
7,56E-02	5,11E-04	



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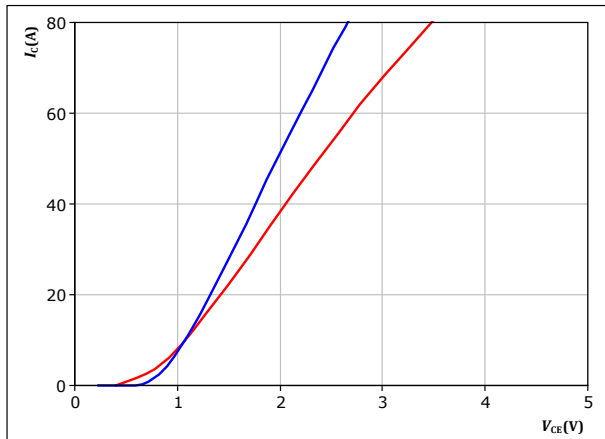
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datasheet

Brake Switch Characteristics

figure 8. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

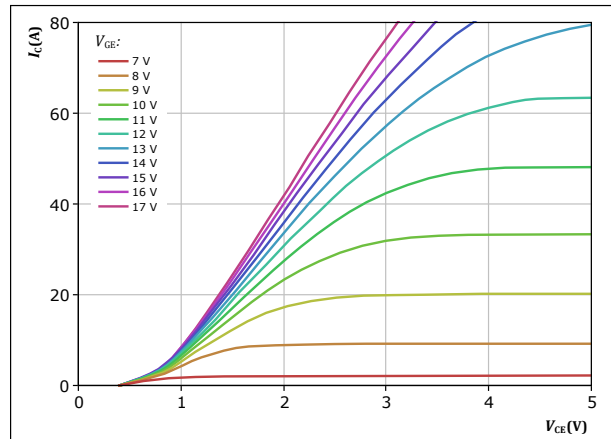


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_J: 25 ^\circ C$ (blue line)
 $125 ^\circ C$ (red line)

figure 9. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

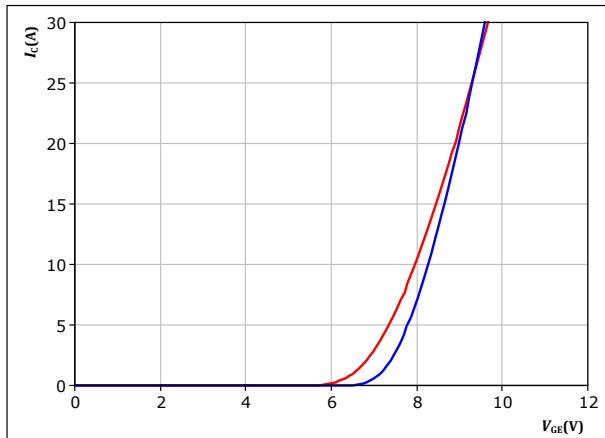


$t_p = 250 \mu s$
 $T_J = 125 ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 10. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

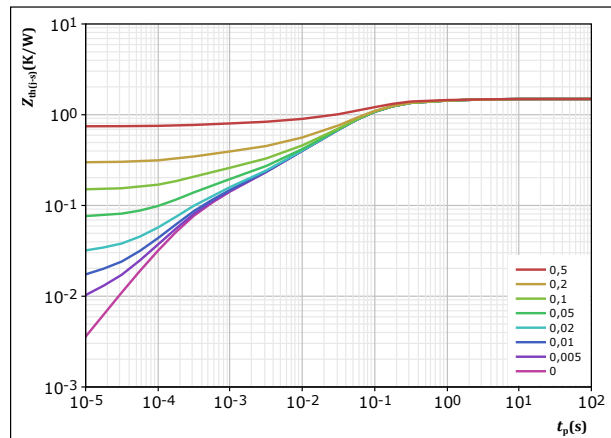


$t_p = 250 \mu s$
 $V_{CE} = 10 V$
 $T_J: 25 ^\circ C$ (blue line)
 $125 ^\circ C$ (red line)

figure 11. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-a)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-a)} = 1,49 K/W$
IGBT thermal model values

$R (K/W)$	$\tau (s)$
7,25E-02	2,15E+00
1,02E-01	4,82E-01
6,96E-01	9,49E-02
3,56E-01	3,40E-02
1,42E-01	5,95E-03
4,77E-02	1,04E-03
7,51E-02	2,72E-04



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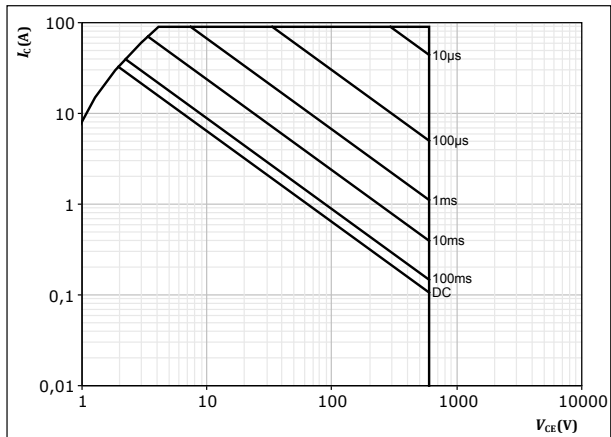
Brake Switch Characteristics

figure 12.

IGBT

Safe operating area

$$I_C = f(V_{CE})$$



D = single pulse

T_s = 80 °C

V_{GE} = 15 V

T_j = T_{jmax}



Brake Diode Characteristics

figure 13. FWD

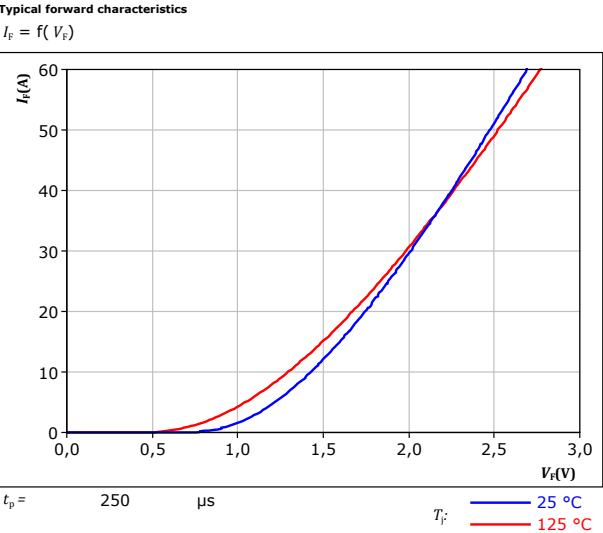
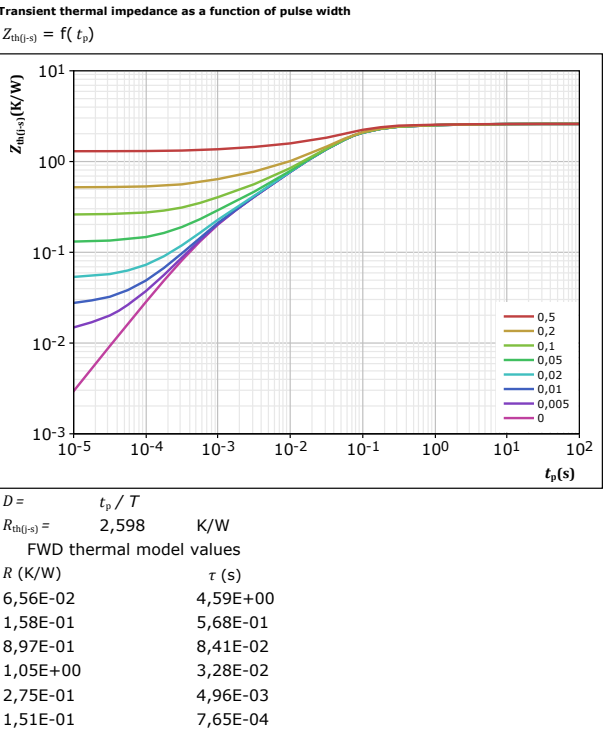


figure 14. FWD





Rectifier Diode Characteristics

figure 15. Rectifier

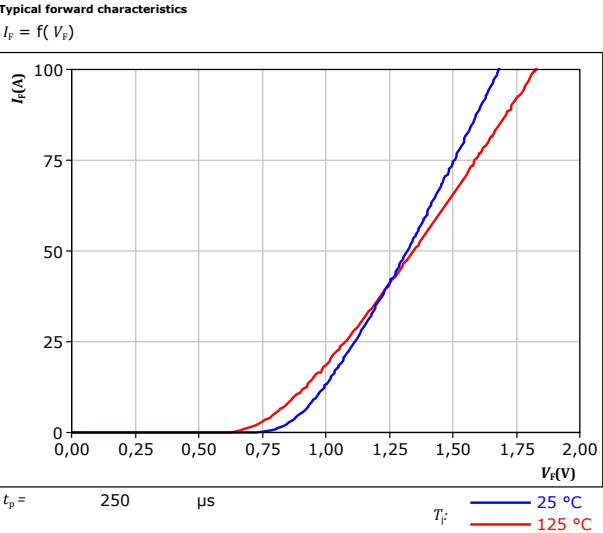
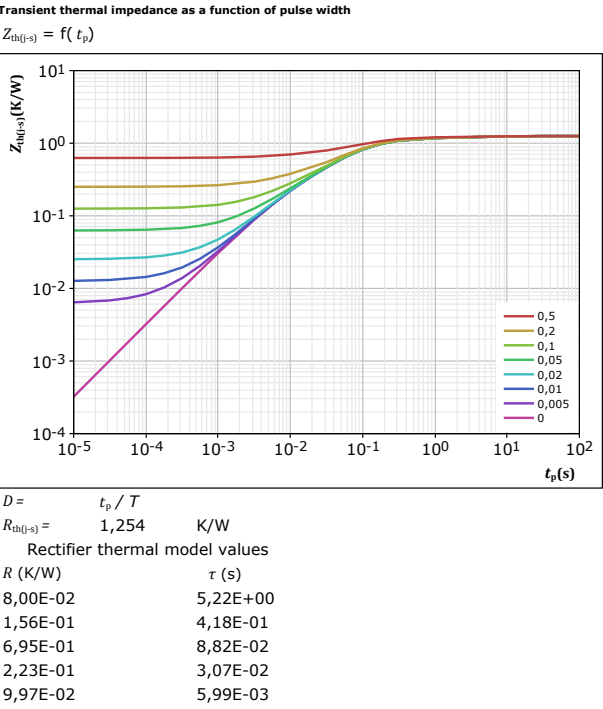


figure 16. Rectifier





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Thermistor Characteristics

figure 17.

Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$





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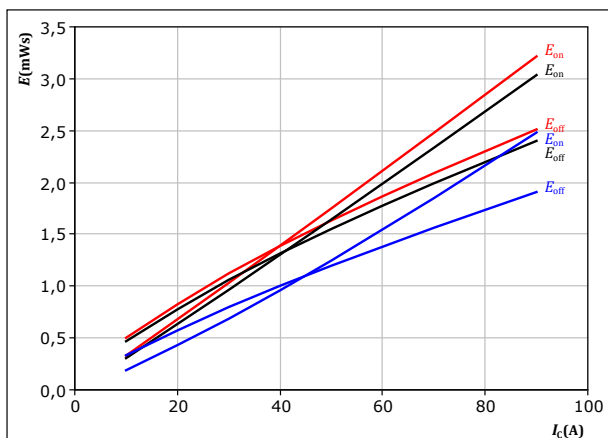
Inverter Switching Characteristics

figure 18.

IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_C)$$



With an inductive load at

$V_{CE} = 350 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$
 $R_{goff} = 16 \text{ } \Omega$

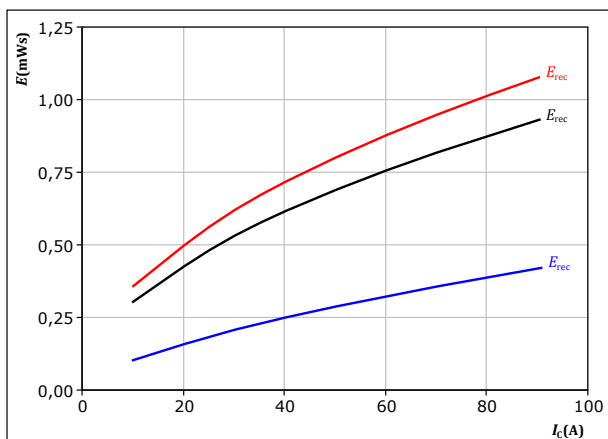
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 20.

FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_C)$$



With an inductive load at

$V_{CE} = 350 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$

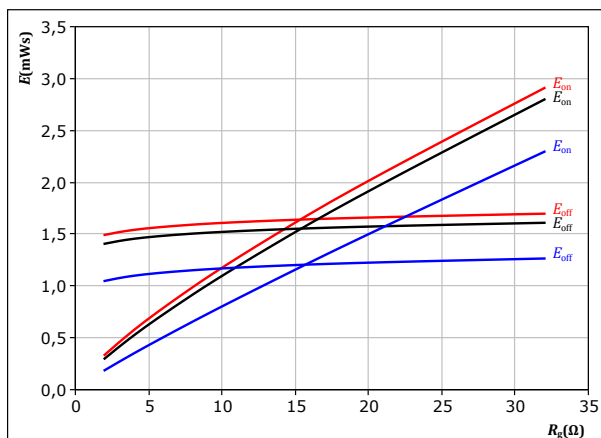
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 19.

IGBT

Typical switching energy losses as a function of IGBT turn on gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 350 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_C = 50 \text{ A}$

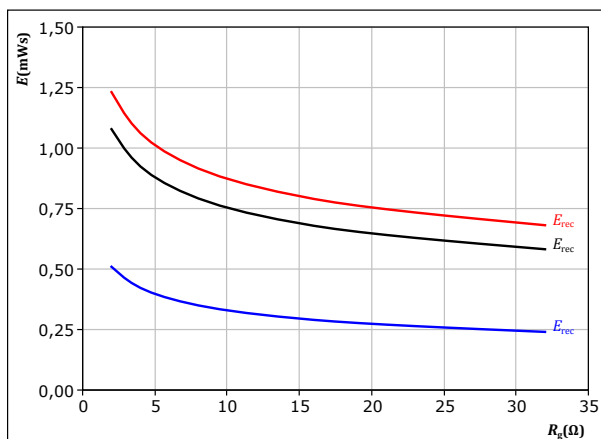
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 21.

FWD

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 350 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_C = 50 \text{ A}$

T_j :
— 25 °C
— 125 °C
— 150 °C



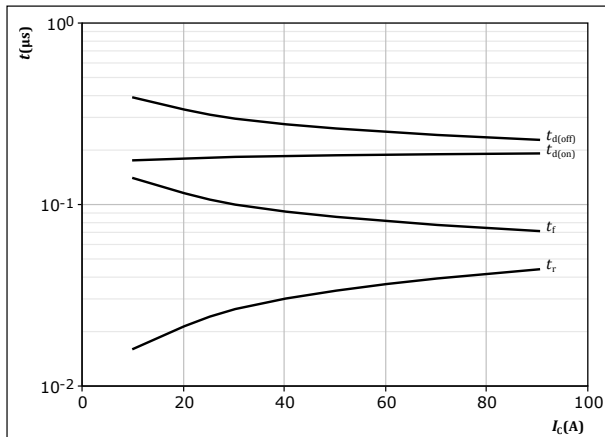
Inverter Switching Characteristics

figure 22.

IGBT

Typical switching times as a function of collector current

$$t = f(I_C)$$



With an inductive load at

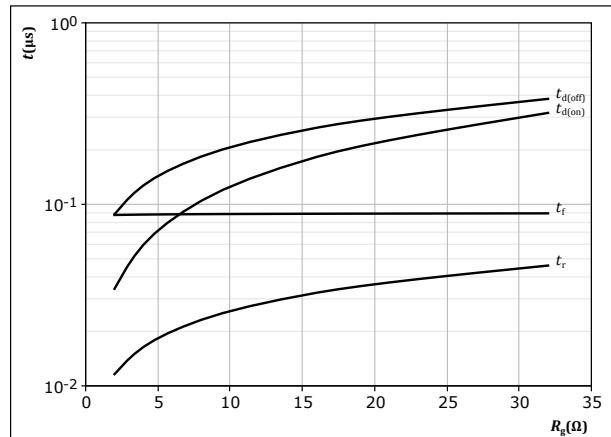
$T_j =$	150	°C
$V_{CE} =$	350	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω
$R_{goff} =$	16	Ω

figure 23.

IGBT

Typical switching times as a function of IGBT turn on gate resistor

$$t = f(R_g)$$



With an inductive load at

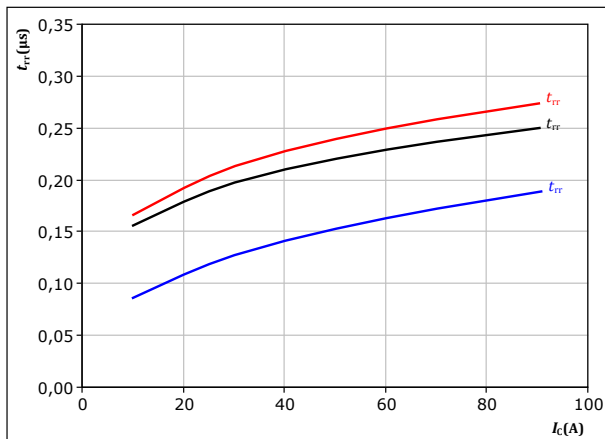
$T_j =$	150	°C
$V_{CE} =$	350	V
$V_{GE} =$	±15	V
$I_C =$	50	A

figure 24.

FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_C)$$



With an inductive load at

$V_{CE} =$	350	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω

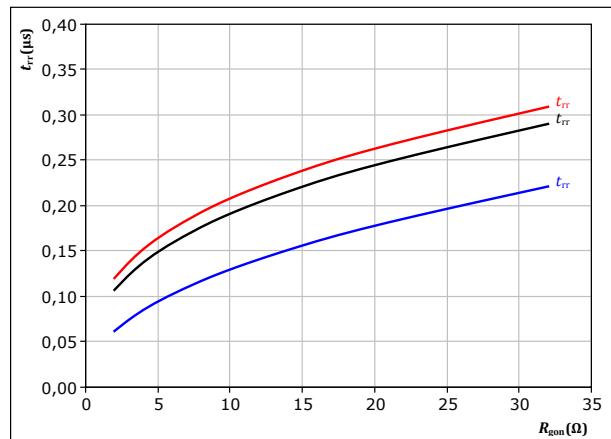
$T_j:$	25 °C
	125 °C
	150 °C

figure 25.

FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$



With an inductive load at

$V_{CE} =$	350	V
$V_{GE} =$	±15	V
$I_C =$	50	A

$T_j:$	25 °C
	125 °C
	150 °C



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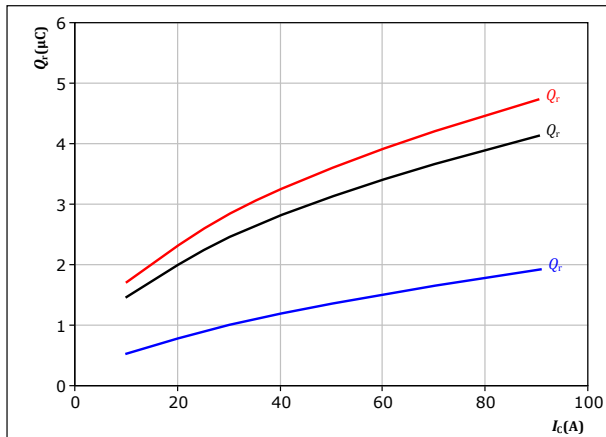
Inverter Switching Characteristics

figure 26.

FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

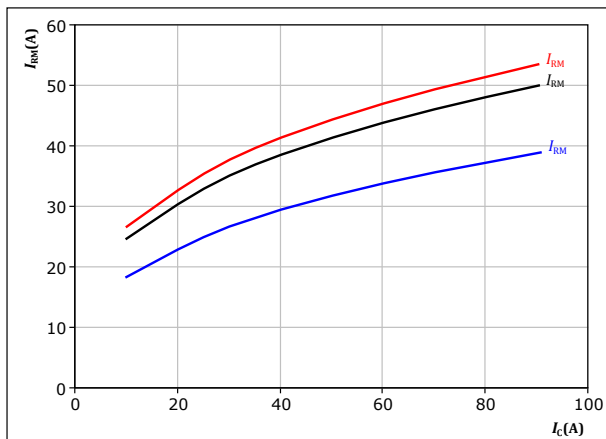
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 28.

FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

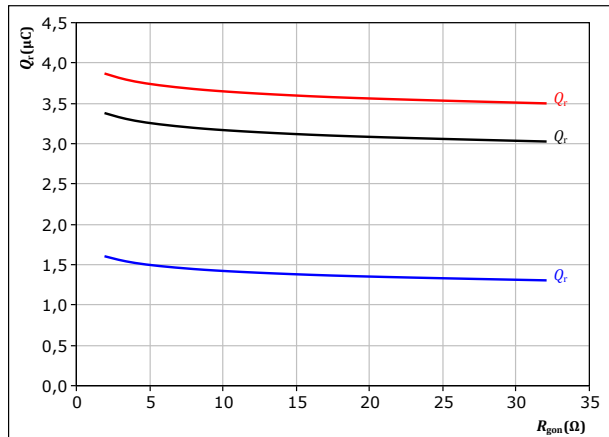
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 27.

FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$



With an inductive load at

$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $I_c = 50$ A

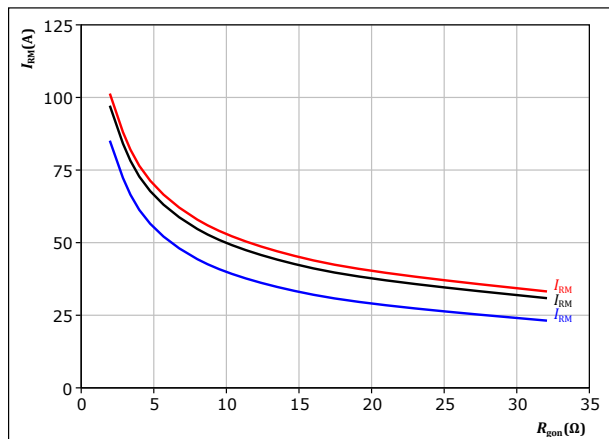
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 29.

FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $I_c = 50$ A

T_j :
— 25 °C
— 125 °C
— 150 °C



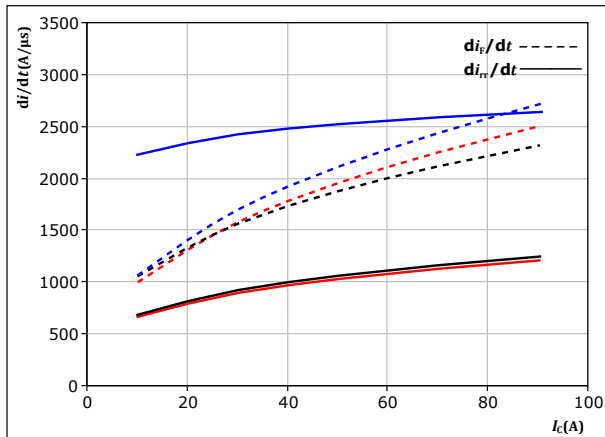
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V23990-P586-A20Y
datasheet

Inverter Switching Characteristics

figure 30. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_C)$



With an inductive load at

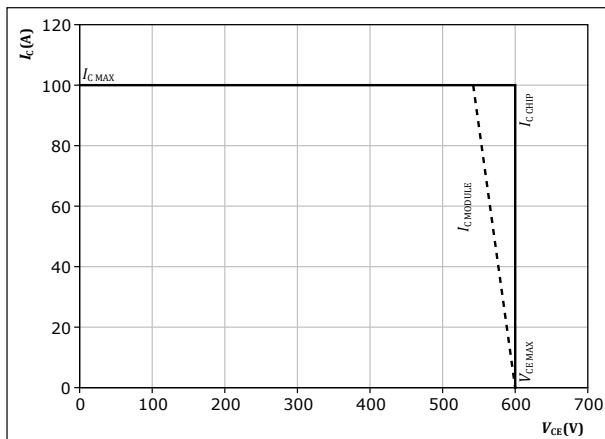
$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

T_j : 25 °C
125 °C
150 °C

figure 32. IGBT

Reverse bias safe operating area

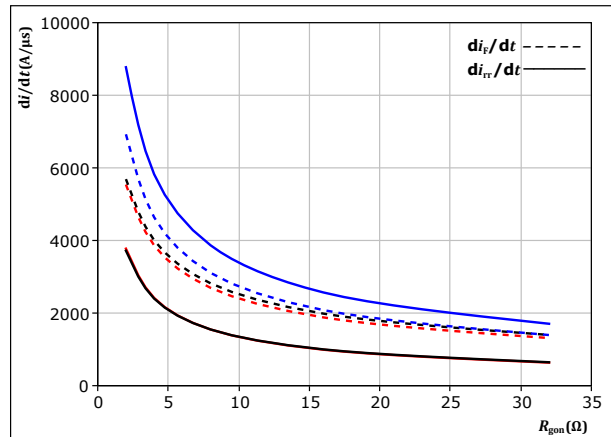
$I_C = f(V_{CE})$



At $T_j = 150$ °C
 $R_{gon} = 16$ Ω
 $R_{goff} = 16$ Ω

figure 31. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



With an inductive load at

$V_{CE} = 350$ V
 $V_{GE} = \pm 15$ V
 $I_C = 50$ A

T_j : 25 °C
125 °C
150 °C



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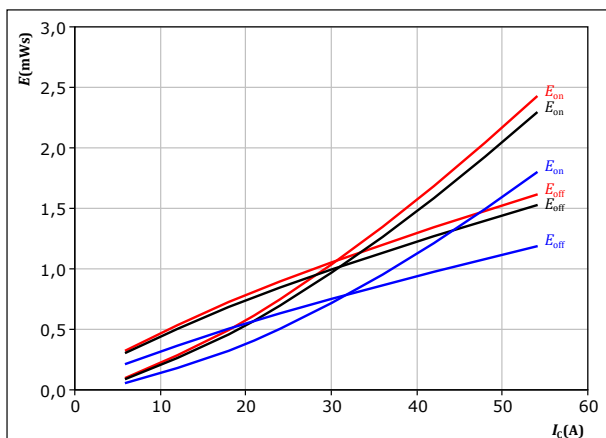
Brake Switching Characteristics

figure 33.

IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_c)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω

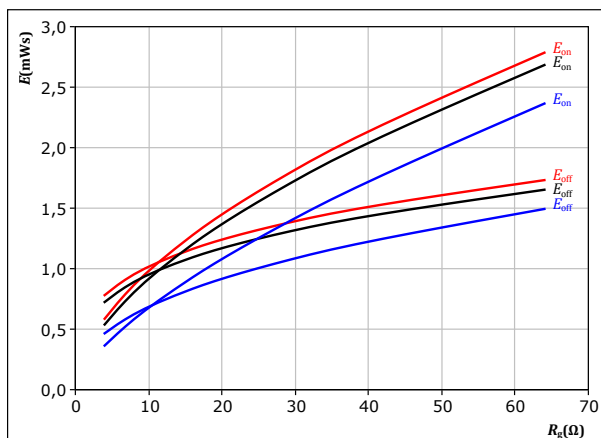
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 34.

IGBT

Typical switching energy losses as a function of IGBT turn on gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

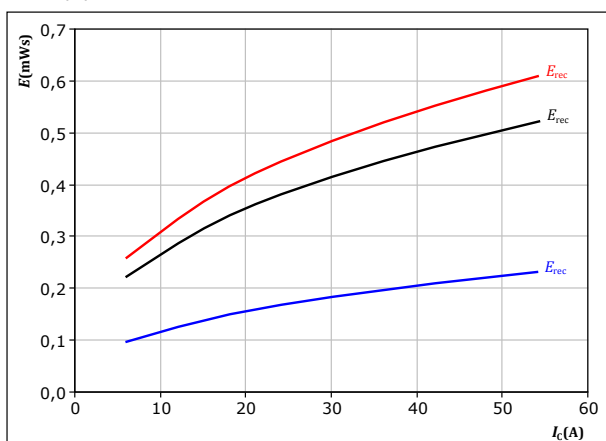
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 35.

FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_c)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω

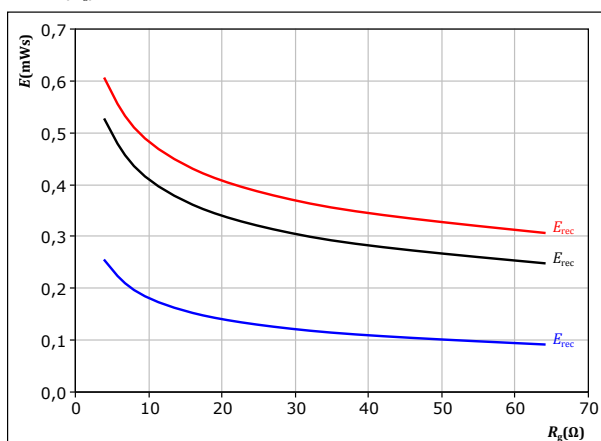
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 36.

FWD

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

T_j :
— 25 °C
— 125 °C
— 150 °C



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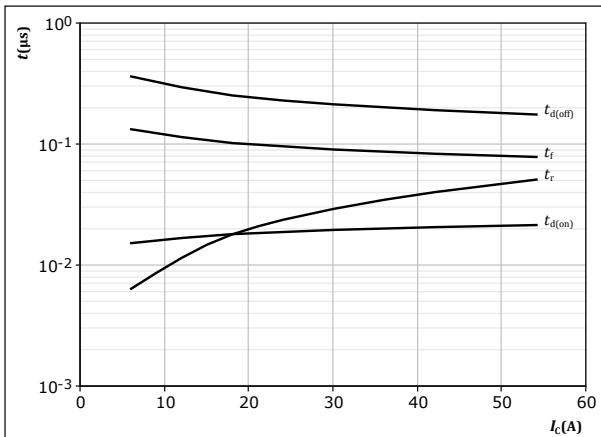
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datasheet

Brake Switching Characteristics

figure 37.

IGBT

Typical switching times as a function of collector current
 $t = f(I_C)$



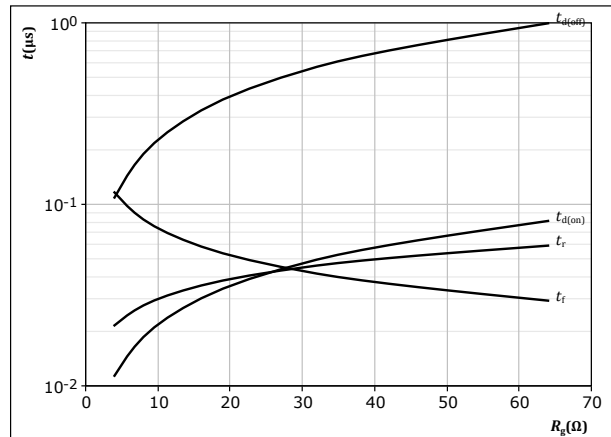
With an inductive load at

$T_j = 150$ °C
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω

figure 38.

IGBT

Typical switching times as a function of IGBT turn on gate resistor
 $t = f(R_g)$



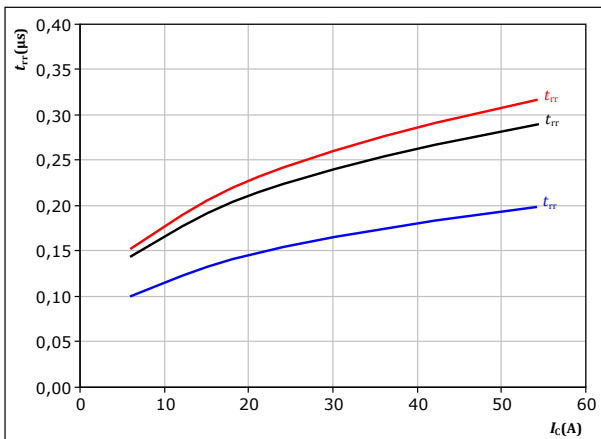
With an inductive load at

$T_j = 150$ °C
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_C = 30$ A

figure 39.

FWD

Typical reverse recovery time as a function of collector current
 $t_{rr} = f(I_C)$



With an inductive load at

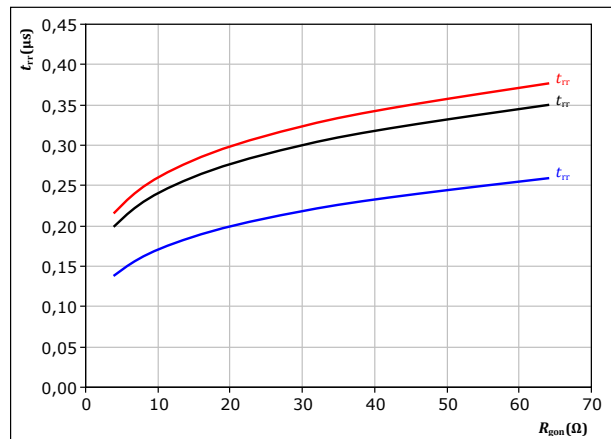
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω

T_j : — 25 °C
— 125 °C
— 150 °C

figure 40.

FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor
 $t_{rr} = f(R_{gon})$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_C = 30$ A

T_j : — 25 °C
— 125 °C
— 150 °C



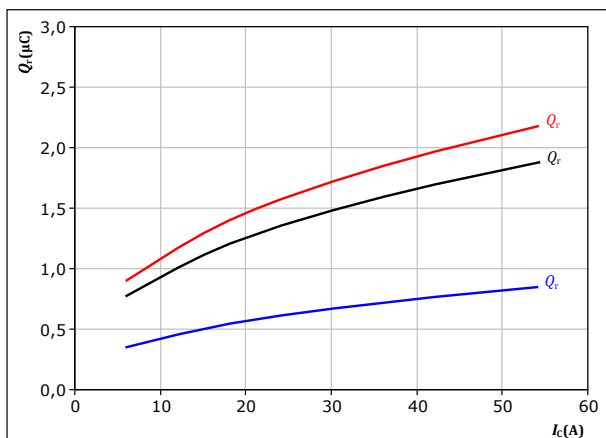
Brake Switching Characteristics

figure 41.

FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω

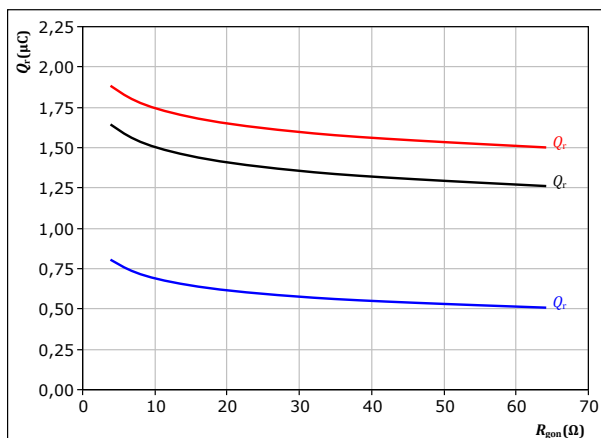
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 42.

FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

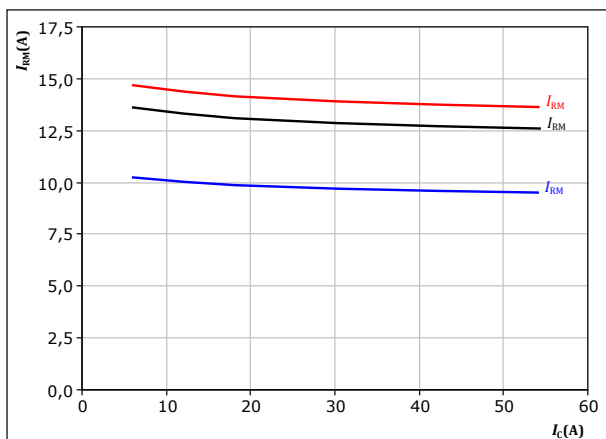
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 43.

FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω

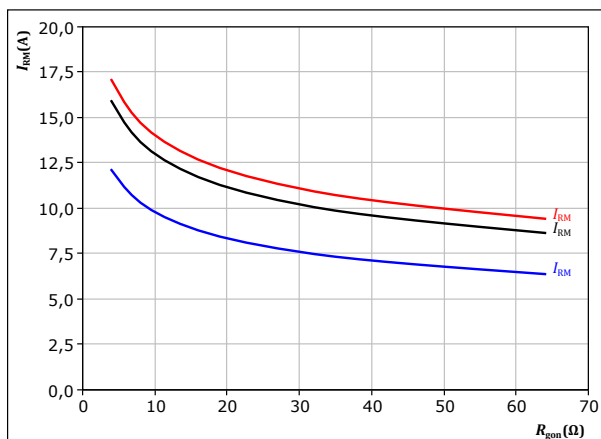
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 44.

FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

T_j :
— 25 °C
— 125 °C
— 150 °C



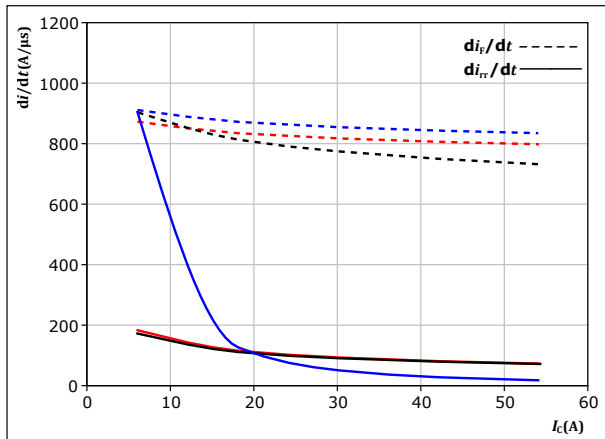
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datasheet

Brake Switching Characteristics

figure 45. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_C)$

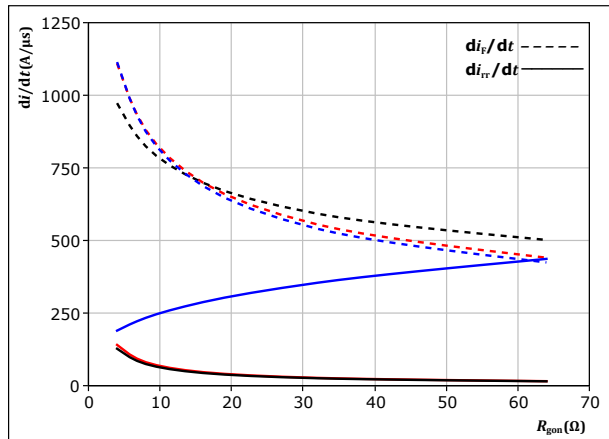


With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω
 $T_j = 25$ °C
 $T_j = 125$ °C
 $T_j = 150$ °C

figure 46. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



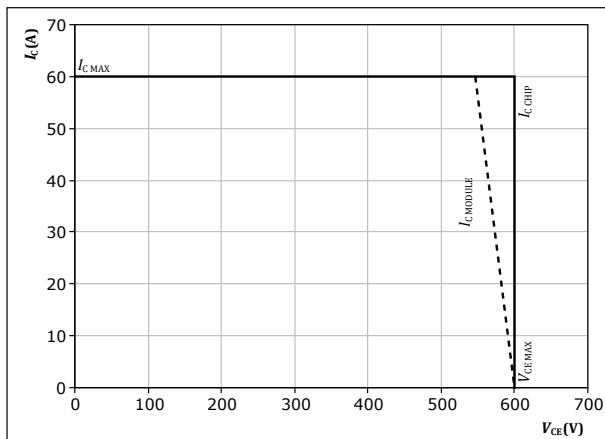
With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_C = 30$ A
 $T_j = 25$ °C
 $T_j = 125$ °C
 $T_j = 150$ °C

figure 47. IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At $T_j = 150$ °C
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω



Switching Definitions

figure 48. IGBT

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})



figure 49. IGBT

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})



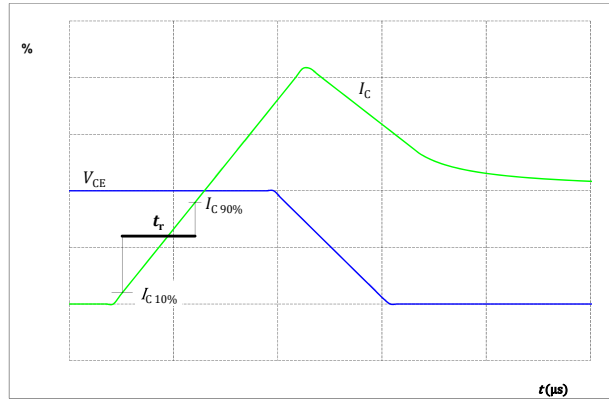
figure 50. IGBT

Turn-off Switching Waveforms & definition of t_f



figure 51. IGBT

Turn-on Switching Waveforms & definition of t_r





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Switching Definitions

figure 52. FWD
Turn-off Switching Waveforms & definition of t_{rr}

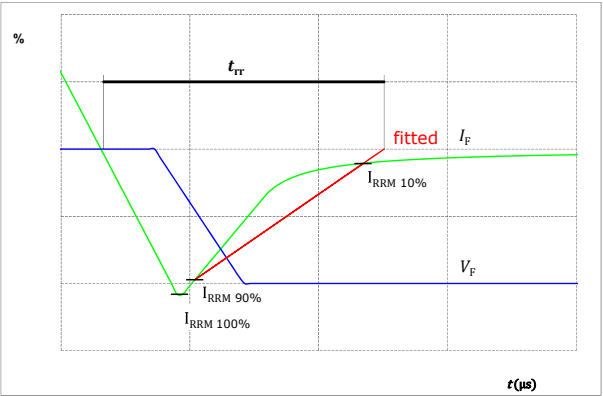
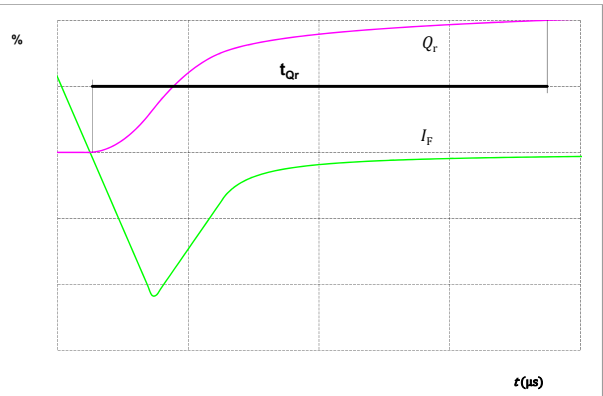


figure 53. FWD
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)






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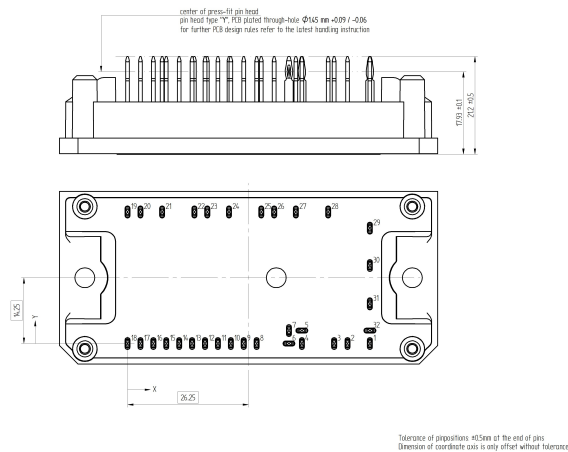
V23990-P586-A20Y

datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	V23990-P586-A20Y
With thermal paste (5,2 W/mK, PTM6000HV)	V23990-P586-A20Y-/7/
With thermal paste (3,4 W/mK, PSX-P7)	V23990-P586-A20Y-/3/

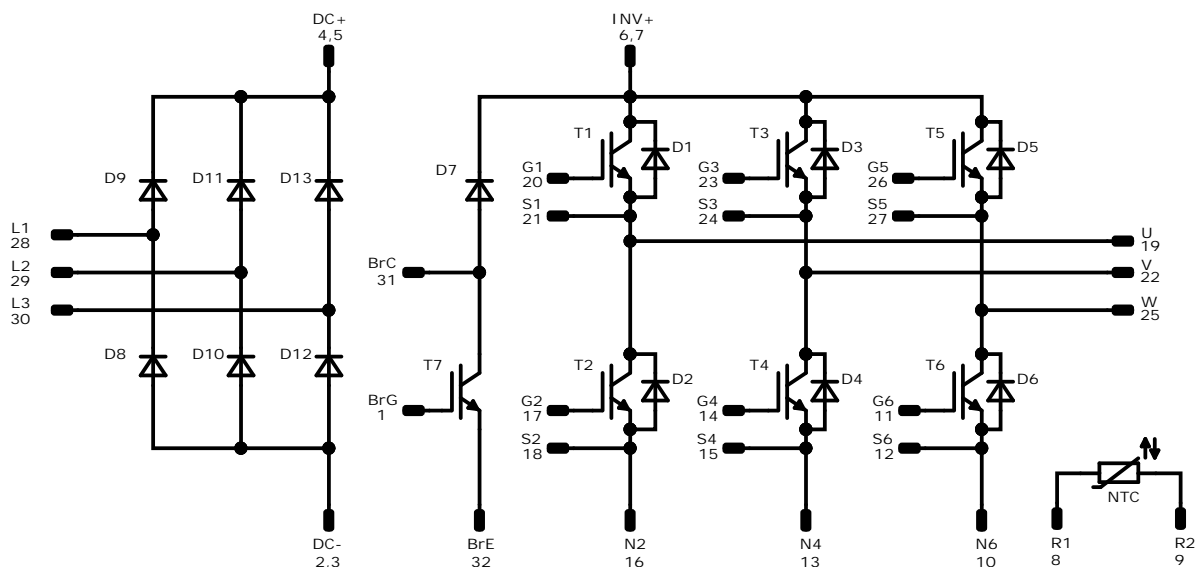
Marking							
	Text	VIN	Date code	Type&Ver	UL	Lot	Serial
		VIN	WWYY	TTTTITVV	UL	LLLL	SSSS
	Datamatrix	Type&Ver	Lot number	Serial	Date code		
		TTTTITVV	LLLL	SSSS	WWYY		

Outline				
Pin table [mm]				
Pin	X	Y	Function	
1	52,55	0	BrG	
2	47,7	0	DC-	
3	44,8	0	DC-	
4	37,8	0	DC+	
5	37,8	2,8	DC+	
6	35	0	Inv+	
7	35	2,8	Inv+	
8	28	0	R1	
9	25,2	0	R2	
10	22,4	0	N6	
11	19,6	0	G6	
12	16,8	0	S6	
13	14	0	N4	
14	11,2	0	G4	
15	8,4	0	S4	
16	5,6	0	N2	
17	2,8	0	G2	
18	0	0	S2	
19	0	28,5	U	
20	2,8	28,5	G1	
21	7,5	28,5	S1	
22	14,5	28,5	V	
23	17,3	28,5	G3	
24	22	28,5	S3	
25	29	28,5	W	
26	31,8	28,5	G5	
27	36,5	28,5	S5	
28	43,5	28,5	L1	
29	52,55	25	L2	
30	52,55	16,9	L3	
31	52,55	8,6	BrC	
32	52,55	2,8	BrE	





Pinout



Identification					
ID	Component	Voltage	Current	Function	Comment
T2, T1, T4, T3, T6, T5	IGBT	600 V	50 A	Inverter Switch	
D1, D2, D3, D4, D5, D6	FWD	600 V	50 A	Inverter Diode	
T7	IGBT	600 V	30 A	Brake Switch	
D7	FWD	600 V	20 A	Brake Diode	
D8, D9, D10, D11, D12, D13	Rectifier	1600 V	35 A	Rectifier Diode	
NTC	NTC			Thermistor	



Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow 1</i> packages see vincotech.com website.

Package data
Package data for <i>flow 1</i> packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.



Document No.:	Date:	Modification:	Pages
V23990-P586-A20Y-D6-14	5 May. 2022	Separate datasheet for pressfit pin version & housing	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.